

Amendments to the Specification:

Please replace the first full paragraph on page 13 with the following amended paragraph:

Figure 3A illustrates an alternative approach to forming the construction shown in Figure 4. In this alternative approach, photoresist layer 114 is used as a masking to pattern second silicon nitride layer 112. After this patterning, photoresist layer 114 is removed. The patterned silicon nitride ~~[[114]]~~ layer 112, as shown in Figure 3A, is then used as a masking layer for the ion milling that results in the construction shown in Figure 4.

Please replace the third full paragraph on page 13 with the following amended paragraph:

In an exemplary embodiment, plasma etching, such as reactive ion etching (RIE), can be used for the patterning. The etching extends through third silicon nitride layer 118 and second silicon nitride layer ~~[[114]]~~ 112 to expose electrical contact surfaces 122 on etch stop 110. The etching may also extend part of the way through first silicon nitride layer ~~[[102]]~~ 104.